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United States Patent	12394772
Kind Code	B2
Date of Patent	August 19, 2025
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Molded dies in semiconductor packages and methods of forming same

Abstract

A package includes an interposer having a first redistribution structure; a first die directly bonded to a first surface of the first redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond; a second die directly bonded to the first surface of the first redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond; an encapsulant around the first die and the second die; and a plurality of conductive connectors on a second side of the first redistribution structure opposite to the first die and the second die.

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Appl. No.: 18/366139

Filed: August 07, 2023

Prior Publication Data

Document Identifier	Publication Date
US 20240021597 A1	Jan. 18, 2024

Related U.S. Application Data

division parent-doc US 17383971 20210723 PENDING child-doc US 18366139
us-provisional-application US 63172349 20210408

Publication Classification

Int. Cl.: H01L25/18 (20230101); **H01L23/00** (20060101); **H01L23/31** (20060101); **H01L23/48** (20060101); **H01L23/498** (20060101); **H01L23/538** (20060101); **H01L25/00** (20060101)

U.S. Cl.:

CPC H01L25/18 (20130101); **H01L23/3128** (20130101); **H01L23/481** (20130101); **H01L23/49816** (20130101); **H01L23/5385** (20130101); **H01L24/08** (20130101); **H01L24/80** (20130101); **H01L25/50** (20130101); H01L2224/08225 (20130101); H01L2224/80895 (20130101); H01L2224/80896 (20130101)

Field of Classification Search

USPC: None

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Background/Summary

PRIORITY CLAIM AND CROSS-REFERENCE (1) This application is a divisional of U.S. application Ser. No. 17/383,971, filed on Jul. 23, 2021, which claims the benefit of U.S. Provisional Application No. 63/172,349, filed on Apr. 8, 2021, which applications are hereby incorporated herein by reference.

BACKGROUND

(1) The semiconductor industry has experienced rapid growth due to ongoing improvements in the integration density of a variety of electronic components (e.g., transistors, diodes, resistors, capacitors, etc.). For the most part, improvement in integration density has resulted from iterative reduction of minimum feature size, which allows more components to be integrated into a given area. As the demand for shrinking electronic devices has grown, a need for smaller and more creative packaging techniques of semiconductor dies has emerged. An example of such packaging systems is Package-on-Package (PoP) technology. In a PoP device, a top semiconductor package is stacked on top of a bottom semiconductor package to provide a high level of integration and component density. PoP technology generally enables production of semiconductor devices with enhanced functionalities and small footprints on a printed circuit board (PCB).

Description

BRIEF DESCRIPTION OF THE DRAWINGS

- (1) Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.
- (2) FIG. 1 illustrates a cross-sectional view of an integrated circuit die in accordance with some embodiments.
- (3) FIGS. 2 through 9 illustrate cross-sectional views of intermediate steps during a process for forming a semiconductor package in accordance with some embodiments.
- (4) FIG. 10 illustrates a cross-sectional view of a package in accordance with some embodiments.
- (5) FIGS. 11 through 16 illustrate cross-sectional views of intermediate steps during a process for forming a semiconductor package in accordance with some embodiments.
- (6) FIG. 17 illustrates a cross-sectional view of a package in accordance with some embodiments.

DETAILED DESCRIPTION

(7) The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

(8) Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

(9) In accordance with some embodiments, an interposer structure is provided with semiconductor dies and/or die stacks directly bonded thereto. For example, a hybrid bonding process may be used to form direct metal-to-metal and direct insulator-to-insulator bonds between the interposer structure and other package components (the semiconductor dies and/or die stacks).

Interconnections between the semiconductor dies and/or die stacks may be provided through the hybrid bonds and the interposer. Various embodiments may achieve one or more of the following, non-limiting advantages: finer bump pitch; small form factor (SFF) packages by using hybrid bonds; smaller bonding pitch scalability for chip I/O to realize high density die-to-die interconnects; improved mechanical endurance; improved electrical performance; reduced defects; and increased yield. Further, short die-to-die connection has the benefits of smaller form-factor, higher bandwidth, improved power integrity (PI), improved signal integrity (SI), and lower power consumption.

(10) Various embodiments are described below in a particular context. Specifically, a chip on wafer on substrate type system on integrated chip (SoIC) package is described. However, various embodiments may also be applied to other types of packaging technologies, such as, integrated fan-out (InFO) packages, or the like.

(11) FIG. 1 illustrates a cross-sectional view of an integrated circuit die **50** in accordance with some embodiments. The integrated circuit die **50** will be packaged in subsequent processing to form an integrated circuit package. The integrated circuit die **50** may be a logic die (e.g., central processing unit (CPU), graphics processing unit (GPU), system-on-a-chip (SoC), application processor (AP), microcontroller, etc.), a memory die (e.g., dynamic random access memory (DRAM) die, static random access memory (SRAM) die, etc.), a power management die (e.g., power management integrated circuit (PMIC) die), a radio frequency (RF) die, a sensor die, a micro-electro-mechanical-system (MEMS) die, a signal processing die (e.g., digital signal processing (DSP) die), a front-end die (e.g., analog front-end (AFE) dies), the like, or combinations thereof.

(12) The integrated circuit die **50** may be formed in a wafer, which may include different device regions that are singulated in subsequent steps to form a plurality of integrated circuit dies. The integrated circuit die **50** may be processed according to applicable manufacturing processes to form integrated circuits. For example, the integrated circuit die **50** includes a semiconductor substrate **52**, such as silicon, doped or undoped, or an active layer of a semiconductor-on-insulator (SOI) substrate. The semiconductor substrate **52** may include other semiconductor materials, such as germanium; a compound semiconductor including silicon carbide, gallium arsenic, gallium

phosphide, indium phosphide, indium arsenide, and/or indium antimonide; an alloy semiconductor including SiGe, GaAsP, AlInAs, AlGaAs, GaInAs, GaInP, and/or GaInAsP; or combinations thereof. Other substrates, such as multi-layered or gradient substrates, may also be used. The semiconductor substrate **52** has an active surface (e.g., the surface facing upwards in FIG. **1**), sometimes called a front side, and an inactive surface (e.g., the surface facing downwards in FIG. **1**), sometimes called a back side.

(13) Devices (represented by a transistor) **54** may be formed at the front surface of the semiconductor substrate **52**. The devices **54** may be active devices (e.g., transistors, diodes, etc.), capacitors, resistors, etc. An inter-layer dielectric (ILD) **56** is over the front surface of the semiconductor substrate **52**. The ILD **56** surrounds and may cover the devices **54**. The ILD **56** may include one or more dielectric layers formed of materials such as Phospho-Silicate Glass (PSG), Boro-Silicate Glass (BSG), Boron-Doped Phospho-Silicate Glass (BPSG), undoped Silicate Glass (USG), or the like.

(14) Conductive plugs **58** extend through the ILD **56** to electrically and physically couple the devices **54**. For example, when the devices **54** are transistors, the conductive plugs **58** may couple the gates and source/drain regions of the transistors. The conductive plugs **58** may be formed of tungsten, cobalt, nickel, copper, silver, gold, aluminum, the like, or combinations thereof. An interconnect structure **60** is over the ILD **56** and conductive plugs **58**. The interconnect structure **60** interconnects the devices **54** to form an integrated circuit. The interconnect structure **60** may be formed by, for example, metallization patterns in dielectric layers on the ILD **56**. The metallization patterns include metal lines and vias formed in one or more low-k dielectric layers. The metallization patterns of the interconnect structure **60** are electrically coupled to the devices **54** by the conductive plugs **58**.

(15) The integrated circuit die **50** further includes pads **62**, such as aluminum pads, to which external connections are made. The pads **62** are on the active side of the integrated circuit die **50**, such as in and/or on the interconnect structure **60**. One or more passivation films **64** are on the integrated circuit die **50**, such as on portions of the interconnect structure **60** and pads **62**. Openings extend through the passivation films **64** to the pads **62**.

(16) Die connectors **66**, such as conductive pillars (for example, formed of a metal such as copper), extend through the openings in the passivation films **64** and are physically and electrically coupled to respective ones of the pads **62**. The die connectors **66** may be formed by, for example, plating, or the like. The die connectors **66** electrically couple the respective integrated circuits of the integrated circuit die **50**.

(17) The connectors **66** may be surrounded by a dielectric layer **68**, which laterally encapsulates the die connectors **66**, and is laterally coterminous with the integrated circuit die **50**. In subsequent processing steps, the die connectors **66** and the dielectric layer **68** may be used to directly bond the integrated circuit die **50** to another package component (e.g., an interposer structure). Accordingly, the dielectric layer **68** may also be referred to as a bonding layer and may be made of any suitable material for direct bonding such as an oxide (e.g., silicon oxide), a nitride (e.g., silicon nitride), an oxynitride (e.g., silicon oxynitride), or the like. The dielectric layer **68** may be formed, for example, by spin coating, chemical vapor deposition (CVD), atomic layer deposition (ALD), or the like. Initially, the dielectric layer **68** may be deposited to bury the die connectors **66**, such that the topmost surface of the dielectric layer **68** is above the topmost surfaces of the die connectors **66**. A planarization process (e.g., a chemical mechanical polish (CMP), etch back process, or the like) may then be applied to level top surfaces of the die connectors **66** and the dielectric layer **68** such that the die connectors **66** are exposed.

(18) In some embodiments, the integrated circuit die **50** is part of die stack that includes multiple semiconductor substrates **52**. For example, the die stack may be a memory device such as a hybrid memory cube (HMC) module, a high bandwidth memory (HBM) module, or the like that includes multiple memory dies. In such embodiments, the die stack includes multiple integrated circuit die

50 interconnected by through-substrate vias (TSVs), which extend through the substrates **52** of the integrated circuit dies **50**. Each of the semiconductor substrates **52** may (or may not) have an interconnect structure **60**.

(19) FIGS. **2** through **9** illustrate cross-sectional views of intermediate steps during a process for forming a first package component **100**, in accordance with some embodiments. A first package region **100A** and a second package region **100B** are illustrated, and one or more of the integrated circuit dies **50** are packaged to form an integrated circuit package in each of the package regions **100A** and **100B**.

(20) In FIG. **2**, a carrier substrate **102** is provided. The carrier substrate **102** may be a glass carrier substrate, a ceramic carrier substrate, or the like. The carrier substrate **102** may be a wafer, such that multiple packages can be formed on the carrier substrate **102** simultaneously. The carrier substrate **102** may be a bulk material that is free of any active or passive devices, for example.

(21) A redistribution structure **104** may be formed on the carrier substrate **102**. In the embodiment shown, the redistribution structure **104** includes a dielectric layer **106**, dielectric layers **108** (labeled **108A**, **108B**, and **108C**), and metallization patterns (sometimes referred to as redistribution layers or redistribution lines, labeled **110A**, **110B**, and **110C**).

(22) The dielectric layer **106** may be formed on the carrier substrate **102**. The bottom surface of the dielectric layer **106** may be in contact with the top surface of the carrier substrate **102**. In some embodiments, the dielectric layer **106** is formed of a polymer, such as polybenzoxazole (PBO), polyimide, benzocyclobutene (BCB), or the like. In other embodiments, the dielectric layer **106** is formed of a nitride such as silicon nitride; an oxide such as silicon oxide, phosphosilicate glass (PSG), borosilicate glass (BSG), boron-doped phosphosilicate glass (BPSG), or the like; or the like. The dielectric layer **106** may be formed by any acceptable deposition process, such as spin coating, CVD, laminating, the like, or a combination thereof. In some embodiments, the dielectric layer **106** may be free of any metallization patterns and protect overlying metallization patterns **110** from damage when the carrier substrate **102** is subsequently removed.

(23) The metallization pattern **110A** may be formed on the dielectric layer **106**. As an example to form metallization pattern **110A**, a seed layer is formed over the dielectric layer **106**. In some embodiments, the seed layer is a metal layer, which may be a single layer or a composite layer comprising a plurality of sub-layers formed of different materials. In some embodiments, the seed layer comprises a titanium layer and a copper layer over the titanium layer. The seed layer may be formed using, for example, physical vapor deposition (PVD) or the like. A photoresist (not shown) is then formed and patterned on the seed layer. The photoresist may be formed by spin coating or the like and may be exposed to light for patterning. The pattern of the photoresist corresponds to the metallization pattern **110A**. The patterning forms openings through the photoresist to expose the seed layer. A conductive material is formed in the openings of the photoresist and on the exposed portions of the seed layer. The conductive material may be formed by plating, such as electroplating or electroless plating, or the like. The conductive material may comprise a metal, like copper, titanium, tungsten, aluminum, or the like. Then, the photoresist and portions of the seed layer on which the conductive material is not formed are removed. The photoresist may be removed by an acceptable ashing or stripping process, such as using an oxygen plasma or the like. Once the photoresist is removed, exposed portions of the seed layer are removed, such as by using an acceptable etching process, such as by wet or dry etching. The remaining portions of the seed layer and conductive material form the metallization pattern **110A**.

(24) The dielectric layer **108A** may be formed on the metallization pattern **110A** and the dielectric layer **106**. In some embodiments, the dielectric layer **108A** is formed of a polymer, which may be a photo-sensitive material such as PBO, polyimide, BCB, or the like, that may be patterned using a lithography mask. In other embodiments, the dielectric layer **108A** is formed of a nitride such as silicon nitride; an oxide such as silicon oxide, PSG, BSG, BPSG; or the like. The dielectric layer **108A** may be formed by spin coating, lamination, CVD, the like, or a combination thereof. The

dielectric layer **108A** is then patterned to form openings exposing portions of the metallization pattern **110A**. The patterning may be formed by an acceptable process, such as by exposing the dielectric layer **108A** to light when the dielectric layer **108A** is a photo-sensitive material or by etching using, for example, an anisotropic etch. If the dielectric layer **108A** is a photo-sensitive material, the dielectric layer **108A** can be developed after the exposure.

(25) Alternatively, in other embodiments that are not specifically illustrated, the dielectric layer **108A** may be deposited prior to forming the metallization pattern **110A**. For example, the dielectric layer **108A** may be deposited of a similar material using a similar process as described above. After deposition, a damascene process (e.g., a dual damascene process or a single damascene process) may be used to pattern openings in the dielectric layer **108A**. The patterning of the openings may correspond to a pattern of the metallization pattern **110A**. The metallization pattern **110A** may then be deposited in the openings, e.g., using a plating process. The metallization pattern **110A** may initially overflow the openings, and a planarization process (e.g., a CMP process or the like) may be used to level top the dielectric layer **108A** and the metallization pattern **110A**.

(26) Additional metallization patterns **110B** and **110C** may be formed over the metallization pattern **110A** in dielectric layers **108B** and **108C**, respectively. Specifically, the metallization patterns **110B** are formed in dielectric layers **108B**, which is disposed over the dielectric layer **108A** and the metallization patterns **110A**. Further, the metallization patterns **110C** are formed in dielectric layers **108C**, which is disposed over the dielectric layer **108B** and the metallization patterns **110B**. Each of the dielectric layers **108B** and **108C** may be formed of a similar material and using similar processes as described above with respect to the dielectric layer **108A**. Further, each of the metallization patterns **110B** and **110C** may be formed of a similar material and using similar processes as described above with respect to the metallization pattern **110A**.

(27) FIG. 2 illustrates a redistribution structure **104** having a specific number of metallization patterns (e.g., the metallization patterns **110A**, **110B**, and **110C**) for illustrative purposes. In some embodiments, the back-side redistribution structure **104** may include any number of dielectric layers and metallization patterns. If more dielectric layers and metallization patterns are to be formed, steps and processes discussed above may be repeated. The metallization patterns may include one or more conductive elements. The conductive elements may be formed during the formation of the metallization pattern by forming the seed layer and conductive material of the metallization pattern over a surface of the underlying dielectric layer and in the opening of the underlying dielectric layer, thereby interconnecting and electrically coupling various conductive lines. Further, the completed redistribution structure **104** may be free of any active devices and/or free of any passive devices, and the carrier substrate **102** and the redistribution structure **104** may be collectively referred to as an interposer.

(28) In FIG. 3, bonding pads **114** of the redistribution structure **104** are formed over the metallization pattern **110C** and the dielectric layer **108C**. The bonding pads **114** are formed for external connection to the redistribution structure **104**. The bonding pads **114** have landing pad portions on and extending along the major surface of the dielectric layer **108C**, and have via portions extending through the dielectric layer **108C** to physically and electrically couple the metallization pattern **110C**. As a result, the UBMs **122** are electrically coupled to the metallization patterns of the redistribution structure **104**. The bonding pads **114** are formed of a similar material and using similar processes as described above with respect to the metallization pattern **110A**. In some embodiments, the bonding pads **114** have a different size (e.g., a different thickness) than the metallization patterns **110A**, **110B**, and **110C**.

(29) Also illustrated in FIG. 3, a bonding layer **112** of the redistribution structure **104** may be formed over the metallization pattern **110C** and the dielectric layer **108C**. The bonding pads **114** may be disposed in the bonding layer **112**. The bonding layer **112** may be any material suitable for achieving a dielectric-to-dielectric bond. For example, the bonding layer **112** may comprise silicon oxide, silicon nitride, silicon oxynitride, or the like, and the bonding layer **112** may be deposited

using a suitable deposition process such as PVD, CVD, ALD, or the like. A planarization step may then be performed to substantially level surfaces of the bonding pads **114** and the bonding layer **112**.

(30) In FIG. **4**, integrated circuit dies **50** (e.g., a first integrated circuit die **50A**, a second integrated circuit die **50B**, and a plurality of stacked integrated circuit dies **50C**) are bonded to the redistribution structure **104** through the bonding pads **114** and the bonding layer **112**. A desired type and quantity of integrated circuit dies **50** are adhered in each of the package regions **100A** and **100B**. In the embodiment shown, multiple integrated circuit dies **50** are adhered adjacent one another. The first and second integrated circuit dies **50A** and **50B** may be a logic device, such as a central processing unit (CPU), a graphics processing unit (GPU), a system-on-a-chip (SoC), a microcontroller, or the like. The plurality of stacked integrated circuit dies **50C** (sometimes referred to as a die stack) may be a memory device, such as a dynamic random access memory (DRAM) die, a static random access memory (SRAM) die, a hybrid memory cube (HMC) module, a high bandwidth memory (HBM) module, or the like. In some embodiments, the integrated circuit dies **50A** and **50B** may be the same type of dies, such as SoC dies. The first integrated circuit die **50A**, the second integrated circuit die **50B**, and the plurality of stacked integrated circuit dies **50C** may be formed in processes of a same technology node, or may be formed in processes of different technology nodes. For example, the first integrated circuit die **50A** may be of a more advanced process node than the second integrated circuit die **50B** and/or the stacked integrated circuit dies **50C**. The integrated circuit dies **50A** and **50B** may have different sizes (e.g., different heights and/or surface areas), or may have the same size (e.g., same heights and/or surface areas). Other combinations of integrated circuit dies (e.g., with or without stacked dies) are also possible in other embodiments.

(31) The integrated circuit dies **50A** and **50B** and the stacked integrated circuit dies are bonded to the redistribution structure **104**, for example, in a hybrid bonding configuration. The integrated circuit dies **50** are disposed face down such that the front sides of the integrated circuit dies **50** face the redistribution structure **104** and the back sides of the integrated circuit dies **50** face away from the redistribution structure **104**. The dielectric layers **68** of the integrated circuit dies **50** may be directly bonded to the bonding layer **112**, and the die connectors **66** of the integrated circuit dies **50** may be directly bonded to the bonding pads **114**. In an embodiment, the bonds between the dielectric layers **68** and the bonding layer **112** are oxide-to-oxide bonds, or the like. The hybrid bonding process further directly bonds the die connectors **66** of the integrated circuit dies **50** to the bonding pads **114** through direct metal-to-metal bonding. Thus, electrical connection can between the integrated circuit dies **50** and the redistribution structure **104** is provided by the physical and electrical connection of the die connectors **66** and the bonding pads **114**. In some embodiments, the interface also includes dielectric-to-metal interfaces between the integrated circuit dies **50** and the redistribution structure **104** (e.g., where the die connectors **66** and the bonding pads **114** are not perfectly aligned and/or have different widths).

(32) As an example, the hybrid bonding process starts with applying a surface treatment to one or more of the dielectric layers **68** or the bonding layer **112**. The surface treatment may include a plasma treatment. The plasma treatment may be performed in a vacuum environment. After the plasma treatment, the surface treatment may further include a cleaning process (e.g., a rinse with deionized water, or the like) that may be applied to one or more of the dielectric layers **68** or the bonding layer **112**. The hybrid bonding process may then proceed to aligning the die connectors **66** to the bonding pads **114**. When the integrated circuit dies **50** and the redistribution structure **104** are aligned, the die connectors **66** may overlap with the corresponding bonding pads **114**. Next, the hybrid bonding includes a pre-bonding step, during which each integrated circuit die **50** is put in contact with the bonding layer **112** and respective bonding pads **114**. The pre-bonding may be performed at room temperature (e.g., between about 21° C. and about 25° C.). The hybrid bonding process continues with performing an anneal, for example, at a temperature between about 150° C.

and about 400° C. for a duration between about 0.5 hours and about 3 hours, so that the metal in die connectors **55** (e.g., copper) and the metal of the bonding pads **114** (e.g., copper) inter-diffuses to each other, and hence the direct metal-to-metal bonding is formed. Other direct bonding processes (e.g., using adhesives, polymer-to-polymer bonding, or the like) may be used in other embodiments.

(33) Notably, the integrated circuit dies **50** are bonded to the redistribution structure **104** without the use of solder connections (e.g., microbumps or the like). By directly bonding the integrated circuit dies **50** to the redistribution structure **104**, advantages can be achieved, such as, finer bump pitch; small form factor packages by using hybrid bonds; smaller bonding pitch scalability for chip I/O to realize high density die-to-die interconnects; improved mechanical endurance; improved electrical performance; reduced defects; and increased yield. Further, shorter die-to-die may be achieved between the integrated circuit dies **50** and has the benefits of smaller form-factor, higher bandwidth, improved power integrity (PI), improved signal integrity (SI), and lower power consumption.

(34) In FIG. 5, an encapsulant **120** is formed on and around the various components. After formation, the encapsulant **120** encapsulates the integrated circuit dies **50**, and the encapsulant **120** may contact a top surface of the bonding layer **112**. The encapsulant **120** may be a molding compound, epoxy, or the like. The encapsulant **120** may be applied by compression molding, transfer molding, or the like, and may be formed over the redistribution structure **104** such that the integrated circuit dies **50** are buried or covered. The encapsulant **120** is further formed in gap regions between the integrated circuit dies **50**. The encapsulant **120** may be applied in liquid or semi-liquid form and then subsequently cured.

(35) After the encapsulant **120** is formed, a planarization process is performed on the encapsulant **120** to one or more of the integrated circuit dies **50** (e.g., the stacked integrated circuit dies **50C**). The planarization process may also remove material of the integrated circuit dies **50** that are exposed while other ones of the integrated circuit dies (e.g., the integrated circuit dies **50A** and **50B**) may remain buried in the encapsulant **120** after planarization. A top surface of the encapsulant **120** is substantially coplanar after the planarization process within process variations. The planarization process may be, for example, a chemical-mechanical polish (CMP), a grinding process, or the like. In some embodiments, the planarization may be omitted. After the planarization process, the encapsulant **120** may have a thickness **T1** in a range of about 50 μm to about 1000 μm, or of about 300 μm to about 500 μm. The thickness **T1** may correspond to a maximum standoff height of the integrated circuit dies **50**, and the thickness **T1** may be advantageously reduced in the described embodiments as a result of bonding the integrated circuit dies **50** to the redistribution structure **104** without solder connections.

(36) In FIG. 6, the substrate **102** is removed to expose the dielectric layer **106** of the redistribution structure **104**. Removing the substrate **102** may be performed using any suitable process, such as a grinding process, a CMP process, an etch back process, combinations thereof or the like. A temporary handle (not explicitly illustrated), such as a glass carrier substrate or the like, may be attached to a surface of the encapsulant **120** opposite to the redistribution structure **104** by a die attach film (DAF), or the like. The temporary handle may be subsequently removed after the redistribution structure **104** is bonded to another device component such as package substrate **200**, see FIG. 9.

(37) In FIG. 7, under bump metallizations (UBMs) **122** are formed for external connection to the redistribution structure **104**. The UBMs **122** have bump portions on and extending along the major surface of the dielectric layer **106**, and have via portions extending through the dielectric layer **106** to physically and electrically couple the metallization pattern **110A**. As a result, the UBMs **122** are electrically coupled to the integrated circuit dies **50**.

(38) As an example of forming the UBMs **122**, openings are formed through the dielectric layer **106** to expose portions of the metallization pattern **110A**. The openings may be formed, for

example, using laser drilling, etching, or the like. The conductive UBMs **122** are formed in the openings. In some embodiments, the UBMs **122** comprise flux and are formed in a flux dipping process. In some embodiments, the UBMs **122** comprise a conductive paste such as solder paste, silver paste, or the like, and are dispensed in a printing process. In some embodiments, the UBMs **122** are formed in a manner similar to the metallization pattern **110A**, and may be formed of a similar material as the metallization pattern **110A**. In some embodiments, the UBMs **122** have a different size than the metallization patterns **110A**, **110B**, and **110C**. For example, the UBMs **122** may be thicker than the metallization patterns **110A**, **110B**, and/or **110C**.

(39) Also illustrated in FIG. 7, conductive connectors **124** are formed on the UBMs **122**. The conductive connectors **124** may be ball grid array (BGA) connectors, solder balls, metal pillars, controlled collapse chip connection (C4) bumps, micro bumps, electroless nickel-electroless palladium-immersion gold technique (ENEPIG) formed bumps, or the like. The conductive connectors **124** may include a conductive material such as solder, copper, aluminum, gold, nickel, silver, palladium, tin, the like, or a combination thereof. In some embodiments, the conductive connectors **124** are formed by initially forming a layer of solder through evaporation, electroplating, printing, solder transfer, ball placement, or the like. Once a layer of solder has been formed on the structure, a reflow may be performed in order to shape the material into the desired bump shapes. In another embodiment, the conductive connectors **124** comprise metal pillars (such as a copper pillar) formed by sputtering, printing, electro plating, electroless plating, CVD, or the like. The metal pillars may be solder free and have substantially vertical sidewalls. In some embodiments, a metal cap layer is formed on the top of the metal pillars. The metal cap layer may include nickel, tin, tin-lead, gold, silver, palladium, indium, nickel-palladium-gold, nickel-gold, the like, or a combination thereof and may be formed by a plating process.

(40) In FIG. 8, a singulation process is performed by sawing along scribe line regions, e.g., between the first package region **100A** and the second package region **100B**. The sawing singulates the first package region **100A** from the second package region **100**. The resulting, singulated device **100** is from one of the first package region **100A** or the second package region **100**.

(41) In FIG. 9, each singulated first package component **100** may be mounted to a package substrate **200** using the conductive connectors **124**. The package substrate **200** includes a substrate core **202** and bond pads **204** over the substrate core **202**. The substrate core **202** may be made of a semiconductor material such as silicon, germanium, diamond, or the like. Alternatively, compound materials such as silicon germanium, silicon carbide, gallium arsenic, indium arsenide, indium phosphide, silicon germanium carbide, gallium arsenic phosphide, gallium indium phosphide, combinations of these, and the like, may also be used. Additionally, the substrate core **202** may be an SOI substrate. Generally, an SOI substrate includes a layer of a semiconductor material such as epitaxial silicon, germanium, silicon germanium, SOI, SGOI, or combinations thereof. The substrate core **202** is, in one alternative embodiment, based on an insulating core such as a fiberglass reinforced resin core. One example core material is fiberglass resin such as FR4. Alternatives for the core material include bismaleimide-triazine (BT) resin, or alternatively, other PCB materials or films. Build up films such as ABF or other laminates may be used for substrate core **202**.

(42) The substrate core **202** may include active and passive devices (not shown). A wide variety of devices such as transistors, capacitors, resistors, combinations of these, and the like may be used to generate the structural and functional requirements of the design for the device stack. The devices may be formed using any suitable methods.

(43) The substrate core **202** may also include metallization layers and vias (not shown), with the bond pads **204** being physically and/or electrically coupled to the metallization layers and vias. The metallization layers may be formed over the active and passive devices and are designed to connect the various devices to form functional circuitry. The metallization layers may be formed of alternating layers of dielectric material (e.g., low-k dielectric material) and conductive material

(e.g., copper) with vias interconnecting the layers of conductive material and may be formed through any suitable process (such as deposition, damascene, dual damascene, or the like). In some embodiments, the substrate core **202** is substantially free of active and passive devices. Conductive connectors **210** (e.g., ball grid array (BGA) balls, or the like) may be disposed on a surface of the substrate core **202** opposite the first package component **100**. The conductive connectors **210** may allow the package substrate **200** to be attached to another component, such as, a motherboard, a printed circuit board (PCB), or the like.

(44) In some embodiments, the conductive connectors **124** are reflowed to attach the first package component **100** to the bond pads **204**. The conductive connectors **124** electrically and/or physically couple the package substrate **200**, including metallization layers in the substrate core **202**, to the first package component **100**. In some embodiments, a solder resist **206** is formed on the substrate core **202**. The conductive connectors **124** may be disposed in openings in the solder resist **206** to be electrically and mechanically coupled to the bond pads **204**. The solder resist **206** may be used to protect areas of the substrate **202** from external damage.

(45) The conductive connectors **124** may have an epoxy flux (not shown) formed thereon before they are reflowed with at least some of the epoxy portion of the epoxy flux remaining after the first package component **100** is attached to the package substrate **200**. This remaining epoxy portion may act as an underfill to reduce stress and protect the joints resulting from reflowing the conductive connectors **124**. In some embodiments, an underfill **208** may be formed between the first package component **100** and the package substrate **200** and surrounding the conductive connectors **124**. The underfill **208** may be formed by a capillary flow process after the first package component **100** is attached or may be formed by a suitable deposition method before the first package component **100** is attached. Thus, a package **300A** is formed comprising the first package component **100** and the package substrate **200**.

(46) The first package component **100** may be implemented in other device stacks. For example, a chip on wafer on substrate structure is shown, but the first package component **100** may also be implemented in a Package on Package (PoP) configuration (e.g., with an integrated fan-out (InFO) configuration), a Flip Chip Ball Grid Array (FCBGA) package, or the like. Optionally, a lid or heat spreader (not specifically illustrated) may be attached to a surface of the first package component **100** opposite to the substrate.

(47) Other features and processes may also be included. For example, testing structures may be included to aid in the verification testing of the 3D packaging or 3DIC devices. The testing structures may include, for example, test pads formed in a redistribution layer or on a substrate that allows the testing of the 3D packaging or the 3DIC, the use of probes and/or probe cards, and the like. The verification testing may be performed on intermediate structures as well as the final structure. Additionally, the structures and methods disclosed herein may be used in conjunction with testing methodologies that incorporate intermediate verification of known good dies to increase the yield and decrease costs.

(48) In some embodiments, passive devices (e.g., surface mount devices (SMDs), or the like) may also be attached to the first package component **100** (e.g., to the UBMs **122**) or to the package substrate **200** (e.g., to the bond pads **204**). For example, FIG. **10** illustrates a cross-sectional view of a package **300B** having passive devices according to some embodiments. The package **300B** may be similar to the package **300A** where like reference numerals indicate like elements formed by like processes. The passive devices **400** may be surface mount devices (SMDs), or the like and comprise one or more capacitors, inductors, resistors, the like, or combinations thereof. The passive devices **400** may be substantially free of any active devices. The passive devices **400** may be bonded to the metallization pattern **110A** of the redistribution structure **104** using a hybrid bonding process (e.g., similar to that described above with respect to bonding the integrated circuit dies **50** to the redistribution structure **104**). Specifically, a bonding layer **402** of the passive device **400** may be directly bonded to the dielectric layer **108A** of the redistribution structure **104** using dielectric-

to-dielectric bonds, and bonding pads **404** of the passive device **400** may be directly bonded to the metallization pattern **110A** using metal-to-metal bonds. The bonding layer **402** and the bonding pads **404** may be formed of a similar material and of a similar process as the bonding layer **112** and the bonding pads **114**, respectively. The passive devices **400** may be bonded without solder connections (e.g., microbumps or the like) to achieve a smaller form factor in the resulting package **300B**. In some embodiments, the dielectric layer **106** may be removed after removing the substrate **102** to expose the metallization pattern **110A**. In other embodiments, the passive devices **400** may be bonded to the metallization pattern **110A** of the redistribution structure **104** in a flip chip bonding process, for example, by reflowing solder connections between the passive devices **400** and the metallization pattern **110A**.

(49) FIGS. **11** through **15** illustrate cross-sectional views of intermediate steps of forming a package **500A** according to some embodiments. In FIGS. **11** through **14**, a second package component **150** is formed. A first package region **150A** and a second package region **150B** are illustrated, and one or more of the integrated circuit dies **50** are packaged to form an integrated circuit package in each of the package regions **150A** and **150B**. The second package component **150** may be similar to the first package component **100** where like reference numerals indicate like elements formed by like processes.

(50) FIG. **11** illustrates the substrate **102** with the redistribution structure **104** formed thereon using similar processes as described above. The substrate **102** may include through substrate vias (TSVs) **130**, which may be electrically connected to the metallization patterns in the redistribution structure **104**. The through vias **130** may comprise a conductive material (e.g., copper, or the like) and may extend from the redistribution structure **104** into the substrate **102**. Insulating barrier layers (not separately illustrated) may be formed around at least portions of the through vias **130** in the substrate **102**. The insulating barrier layers may comprise, for example, silicon oxide, silicon nitride, silicon oxynitride, or the like, and may be used to physically and electrically isolate the through vias **130** from the substrate **102**. In subsequent processing steps, the substrate **102** may be thinned to expose the through vias **130** (see FIG. **13**). After thinning, the through vias **130** provide electrical connection from a back side of the substrate **102** to a front side of the substrate **102**.

(51) In FIG. **12**, integrated circuit dies **50** (e.g., the first integrated circuit dies the second integrated circuit dies, and the plurality of stacked integrated circuit dies **50C**) are bonded to the redistribution structure **104** using, for example, a hybrid bonding process as described above. By directly bonding the integrated circuit dies **50** to the redistribution structure **104**, advantages can be achieved, such as, finer bump pitch; small form factor packages by using hybrid bonds; smaller bonding pitch scalability for chip I/O to realize high density die-to-die interconnects; improved mechanical endurance; improved electrical performance; reduced defects; and increased yield. Further, shorter die-to-die may be achieved between the integrated circuit dies **50**, which have the benefits of smaller form-factor, higher bandwidth, improved power integrity (PI), improved signal integrity (SI), and lower power consumption. Further illustrated by FIG. **12**, the encapsulant **120** is formed around the integrated circuit dies **150** as described above.

(52) In FIG. **13**, a planarization process is applied to the substrate **102** to expose the through vias **130**. The planarization may remove portions of the substrate **102** opposite to the redistribution structure **104** such that the through vias **130** are exposed. The planarization may be achieved by any suitable process, such as, grinding, CMP, etch back, the like, or combinations thereof. After the planarization, the through vias **130** extend completely through the substrate **120** and provide interconnection from the redistribution structure **104** to a surface of the substrate **120** opposite the redistribution structure **104**.

(53) In FIG. **14**, a redistribution structure **132** is formed on a side of the substrate **102** opposite to the redistribution structure **104**. The redistribution structure **132** includes dielectric layers **134** (labelled **134A**, **134B**, and **134C**) and metallization patterns **136** (sometimes referred to as redistribution layers or redistribution lines, labeled **136A**, **136B** and **136C**). The dielectric layers

134 and the metallization patterns **136** may be made of a similar material and using a similar process as the dielectric layers **108** and the metallization patterns no, respectively. The metallization patterns **136** may be electrically connected to the metallization patterns no by the through vias **130**. Although FIG. **14** illustrates the redistribution structure **132** as having a particular number of dielectric layers **134** and metallization patterns **136**, it should be appreciated that the redistribution structure **132** may be have a different number of dielectric layers **132** and/or metallization patterns **136** in other embodiments. Further, the number of dielectric layers and metallization patterns in the redistribution structure **132** may be the same or different than the number of dielectric layers and metallization patterns in the redistribution structure **104**. The completed redistribution structure **132** may be free of any active devices and/or free of any passive devices, and the carrier substrate **102**, the redistribution structure **104**, and the redistribution structure **132** may be collectively referred to as an interposer.

(54) Also illustrated in FIG. **14**, the UBMs **122** and the conductive connectors **124** may be formed on the redistribution structure **132**. For example, the UBMs **122** and the conductive connectors **124** may be formed on the metallization pattern **136C** of the redistribution structure **132** using a similar material and with a similar process as described above.

(55) In FIG. **15**, a singulation process is performed by sawing along scribe line regions, e.g., between the first package region **150A** and the second package region **150B**. The sawing singulates the first package region **150A** from the second package region **150B**. The resulting, singulated device **150** is from one of the first package region **150A** or the second package region **150B**.

(56) In FIG. **16**, each singulated the second package component **150** may be mounted to a package substrate **200** using the conductive connectors **124**. The package substrate **200** includes a substrate core **202**, bond pads **204** over the substrate core **202**, and conductive connectors **210** on an opposite side of the substrate core **202** as the second package component **150** as described above.

(57) In some embodiments, the conductive connectors **124** are reflowed to attach the second package component **150** to the bond pads **204**. The conductive connectors **124** electrically and/or physically couple the package substrate **200**, including metallization layers in the substrate core **202**, to the second package component **150**. In some embodiments, a solder resist **206** is formed on the substrate core **202**. The conductive connectors **124** may be disposed in openings in the solder resist **206** to be electrically and mechanically coupled to the bond pads **204**. The solder resist **206** may be used to protect areas of the substrate **202** from external damage.

(58) The conductive connectors **124** may have an epoxy flux (not shown) formed thereon before they are reflowed with at least some of the epoxy portion of the epoxy flux remaining after the second package component **150** is attached to the package substrate **200**. This remaining epoxy portion may act as an underfill to reduce stress and protect the joints resulting from reflowing the conductive connectors **124**. In some embodiments, an underfill **208** may be formed between the second package component **150** and the package substrate **200** and surrounding the conductive connectors **124**. The underfill **208** may be formed by a capillary flow process after the second package component **150** is attached or may be formed by a suitable deposition method before the second package component **150** is attached. Thus, a package **500A** is formed comprising the second package component **150** and the package substrate **200**.

(59) The second package component **150** may be implemented in other device stacks. For example, a chip on wafer on substrate structure is shown, but the first package component **100** may also be implemented in a PoP configuration (e.g., with InFO configuration), a FCBGA package, or the like. Optionally, a lid or heat spreader (not specifically illustrated) may be attached to a surface of the second package component **150** opposite to the substrate **200**.

(60) Other features and processes may also be included. For example, testing structures may be included to aid in the verification testing of the 3D packaging or 3DIC devices. The testing structures may include, for example, test pads formed in a redistribution layer or on a substrate that allows the testing of the 3D packaging or the 3DIC, the use of probes and/or probe cards, and the

like. The verification testing may be performed on intermediate structures as well as the final structure. Additionally, the structures and methods disclosed herein may be used in conjunction with testing methodologies that incorporate intermediate verification of known good dies to increase the yield and decrease costs.

(61) In some embodiments, passive devices (e.g., surface mount devices (SMDs), or the like) may also be attached to the second package component **150** (e.g., to the UBMs **122**) or to the package substrate **200** (e.g., to the bond pads **204**). For example, FIG. **17** illustrates a cross-sectional view of a package **500B** having passive devices according to some embodiments. The package **500B** may be similar to the package **500A** where like reference numerals indicate like elements formed by like processes. The passive devices **400** may be surface mount devices (SMDs), or the like and comprise one or more capacitors, inductors, resistors, the like, or combinations thereof. The passive devices **400** may be substantially free of any active devices. The passive devices **400** may be bonded to the metallization pattern **136C** of the redistribution structure **132** using a hybrid bonding process (e.g., similar to that described above with respect to bonding the integrated circuit dies **50** to the redistribution structure **104**). Specifically, a bonding layer **138** may be formed around the UBMs **122**. The bonding layer **132** may be formed of a similar material and using a similar process as the bonding layer **112**. A planarization process may be applied to level surfaces of the bonding layer **138** with the UBMs **122**. Subsequently, a bonding layer **402** of the passive device **400** may be directly bonded to the bonding layer **138** of the redistribution structure **132** using dielectric-to-dielectric bonds, and bonding pads **404** of the passive device **400** may be directly bonded to the UBMs **122** using metal-to-metal bonds. The bonding layer **402** and the bonding pads **404** may be formed of a similar material and of a similar process as the bonding layer **112** and the bonding pads **114**, respectively. The passive devices **400** may be bonded without solder connections (e.g., microbumps or the like) to achieve a smaller form factor in the resulting package **300B**. In other embodiments, the passive devices **400** may be bonded to the UBMs **122** of the redistribution structure **132** in a flip chip bonding process, for example, by reflowing solder connections (e.g., microbumps or the like) between the passive devices **400** and the UBMs **122**.

(62) Various embodiments include an interposer structure with semiconductor dies and/or die stacks directly bonded thereto. For example, a hybrid bonding process may be used to form direct metal-to-metal and direct insulator-to-insulator bonds between the interposer structure and other package components (the semiconductor dies and/or die stacks). Interconnections between the semiconductor dies and/or die stacks may be provided through the hybrid bonds and the interposer. Various embodiments may achieve one or more of the following, non-limiting advantages: finer bump pitch; small form factor (SFF) packages by using hybrid bonds; smaller bonding pitch scalability for chip I/O to realize high density die-to-die interconnects; improved mechanical endurance; improved electrical performance; reduced defects; and increased yield. Further, short die-to-die connection has the benefits of smaller form-factor, higher bandwidth, improved power integrity (PI), improved signal integrity (SI), and lower power consumption.

(63) In some embodiments, a package includes an interposer, wherein the interposer comprises a first redistribution structure; a first die bonded to a first surface of the first redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond; a second die bonded to the first surface of the first redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond; an encapsulant around the first die and the second die; and a plurality of conductive connectors on a second side of the first redistribution structure opposite to the first die and the second die. Optionally, in some embodiments, the package further includes a plurality of stacked dies, wherein the plurality of stacked dies is directly bonded to the first surface of the first redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond. Optionally, in some embodiments, the plurality of conductive connectors physically contacts a second surface of the first redistribution structure that is opposite to the first surface of the first redistribution structure. Optionally, in some embodiments, the package further includes a passive device die

directly bonded to the second surface of the first redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond. Optionally, in some embodiments, the interposer further comprises: a second redistribution structure; a semiconductor substrate between the first redistribution structure and the second redistribution structure; and a plurality of through vias in the semiconductor substrate, wherein the plurality of through vias electrically connect the first redistribution structure to the second redistribution structure. Optionally, in some embodiments, the plurality of conductive connectors contacts a third surface of the second redistribution structure that is opposite to the semiconductor substrate. Optionally, in some embodiments, the package further includes a passive device die directly bonded to the third surface of the second redistribution structure with a dielectric-to-dielectric bond and a metal-to-metal bond.

(64) In some embodiments, a semiconductor package includes a plurality of first dielectric layers, each of the plurality of first dielectric layers having a first metallization pattern disposed therein; a bonding layer over the plurality of first dielectric layers; a plurality of bonding pads in the bonding layer; a first die comprising: a first insulating layer touching the bonding layer; and first conductive pads touching the plurality of bonding pads; a die stack comprising: a second insulating layer touching the bonding layer; and second conductive pads touching the plurality of bonding pads; and an encapsulant over the bonding layer, the encapsulant being disposed around the die stack and the first die. Optionally, in some embodiments, the package further includes a plurality of second dielectric layers, each of the plurality of second dielectric layers having a second metallization pattern disposed therein; a semiconductor substrate between the plurality of first dielectric layers and the plurality of second dielectric layers, wherein the semiconductor substrate is free of any active devices; and a plurality through vias extending through the semiconductor substrate. Optionally, in some embodiments, the package further includes an integrated passive device (IPD) bonded to an opposite side of the plurality of first dielectric layers as the first die and the die stack. Optionally, in some embodiments, the IPD is bonded to the opposite side of the plurality of first dielectric layers as the first die and the die stack without solder connections. Optionally, in some embodiments, the package further includes a package substrate bonded to a same surface as the IPD with a plurality of conductive connectors, wherein the IPD is between the package substrate and the same surface. Optionally, in some embodiments, the same surface is a surface of the plurality of first dielectric layers. Optionally, in some embodiments, the plurality of conductive connectors comprises solder.

(65) In some embodiments, a method includes forming a first redistribution structure over a substrate, wherein the substrate is free of any active devices, and wherein the first redistribution structure comprises: a plurality of first metallization patterns in a plurality of a first dielectric layers; a bonding layer over the first plurality of metallization patterns; and a plurality of bonding pads in the bonding layer, wherein the plurality of bonding pads is electrically connected to the first plurality of metallization patterns. The method further includes bonding a first die to the first redistribution structure, wherein bonding the first die comprises directly bonding a first insulating layer of the first die to the bonding layer and directly bonding first die connectors of the first die to the plurality of bonding pads; bonding a second die to the first redistribution structure, wherein bonding the second die comprises directly bonding a second insulating layer of the second die to the bonding layer and directly bonding second die connectors of the second die to the plurality of bonding pads; and encapsulating the first die and the second die in a molding compound. Optionally, in some embodiments, the method further includes removing the substrate after encapsulating the first die and the second die in the molding compound. Optionally, in some embodiments, the substrate comprises a plurality of through vias electrically connected to the plurality of first metallization patterns, and wherein the method further comprises planarizing a surface of the substrate opposite to the first redistribution structure to expose the plurality of through vias. Optionally, in some embodiments, the method further includes forming a second redistribution structure on the surface of the substrate opposite to the first redistribution structure,

wherein the second redistribution structure comprises a plurality of second metallization patterns in a plurality of second dielectric layers, and wherein the plurality of through vias electrically connect the plurality of first metallization patterns to the plurality of second metallization patterns. Optionally, in some embodiments, the method further includes bonding a integrated passive device (IPD) to a side of the first redistribution structure opposite to the first die and the second die without solder connectors. Optionally, in some embodiments, the second die is disposed in a die stack.

(66) The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

Claims

1. A method comprising: forming a first redistribution structure over a substrate, wherein the substrate is free of any active devices, and wherein the first redistribution structure comprises: a plurality of first metallization patterns in a plurality of first dielectric layers; a bonding layer over the first plurality of metallization patterns; and a plurality of bonding pads in the bonding layer, wherein the plurality of bonding pads is electrically connected to the first plurality of metallization patterns; bonding a first die to the first redistribution structure, wherein bonding the first die comprises directly bonding a first insulating layer of the first die to the bonding layer and directly bonding first die connectors of the first die to the plurality of bonding pads; bonding a second die to the first redistribution structure, wherein bonding the second die comprises directly bonding a second insulating layer of the second die to the bonding layer and directly bonding second die connectors of the second die to the plurality of bonding pads; bonding a die stack to the first redistribution structure, wherein bonding the die stack comprises directly bonding a third insulating layer of the die stack to the bonding layer and directly bonding third die connectors of the die stack to the plurality of bonding pads; encapsulating the first die and the second die in a molding compound; forming a second redistribution structure on a surface of the substrate opposite to the first redistribution structure; and after forming the second redistribution structure, directly bonding an integrated passive device (IPD) to a surface of the second redistribution structure that is opposite to the substrate using a solderless bonding process, wherein the first die and the die stack each overlap the IPD.

2. The method of claim 1, wherein the substrate comprises a plurality of through vias electrically connected to the plurality of first metallization patterns, and wherein the method further comprises planarizing the surface of the substrate opposite to the first redistribution structure to expose the plurality of through vias.

3. The method of claim 2, wherein the second redistribution structure comprises a plurality of second metallization patterns in a plurality of second dielectric layers, wherein planarizing the surface of the substrate opposite to the first redistribution structure is performed prior to forming the second redistribution structure, and wherein the plurality of through vias electrically connect the plurality of first metallization patterns to the plurality of second metallization patterns.

4. The method of claim 1, wherein forming the second redistribution structure comprises: forming first under bump metallizations (UBMs) and second UBMs on a side of the second redistribution structure that is opposite to the substrate; depositing a first insulating bonding layer around the first UBMs and the second UBMs; and forming solder connections on the first UBMs, wherein directly

bonding the IPD to the surface of the second redistribution structure that is opposite to the substrate using the solderless bonding process comprises directly bonding metal pads of the IPD to the second UBMs and directly bonding a second insulating bonding layer of the IPD to the first insulating bonding layer.

5. The method of claim 4 further comprising: bonding the second redistribution structure to a package substrate with the solder connections; and dispensing an underfill between the first redistribution structure and the package substrate.

6. The method of claim 5, wherein the underfill encapsulates the IPD.

7. The method of claim 4, wherein forming the second redistribution structure comprises performing a planarization process to level surfaces of the first insulating bonding layer, the first UBMs, and the second UBMs.

8. A method comprising: forming a first redistribution structure over a substrate, wherein the first redistribution structure comprises: a first insulating bonding layer at a top surface of the first redistribution structure; a first plurality of bonding pads in the first insulating bonding layer; and a third plurality of bonding pads in the first insulating bonding layer; bonding a first die to the top surface of the first redistribution structure, wherein bonding the first die comprises directly bonding a second insulating bonding layer of the first die to the first insulating bonding layer and directly bonding a second plurality of bonding pads of the first die to the first plurality of bonding pads; bonding a die stack to the top surface of the first redistribution structure, wherein bonding the die stack comprises directly bonding a third insulating bonding layer of the die stack to the first insulating bonding layer and directly bonding a fourth plurality of bonding pads of the die stack to the third plurality of bonding pads, wherein the die stack is laterally spaced apart from the first die; encapsulating the first die and the die stack in a molding compound; after encapsulating the first die and the die stack in the molding compound, removing at least a portion of the substrate; forming a second redistribution structure on a surface of the substrate opposite to the first redistribution structure; after forming the second redistribution structure, bonding an integrated passive device to a surface of the second redistribution structure opposite to the substrate using a solderless bonding process, wherein the first die and each die of the die stack overlaps the integrated passive device; and after removing the portion of the substrate, performing a singulation process through the first redistribution structure and the molding compound after bonding the first die to the top surface of the first redistribution structure.

9. The method of claim 8, wherein the first redistribution structure further comprises a fifth plurality of bonding pads in the first insulating bonding layer, the method further comprising: bonding a second die to the top surface of the first redistribution structure, wherein bonding the second die comprises directly bonding a fourth insulating bonding layer of the second die to the first insulating bonding layer and directly bonding a sixth plurality of bonding pads of the second die to the fifth plurality of bonding pads; and encapsulating the second die in the molding compound.

10. The method of claim 8, wherein removing at least the portion of the substrate exposes a plurality of through vias in the substrate.

11. The method of claim 10, wherein forming the second redistribution structure comprises: forming the second redistribution structure after removing at least the portion of the substrate and before performing the singulation process, and wherein the plurality of through vias electrically connects first metallization patterns in the first redistribution structure to second metallization patterns in the second redistribution structure.

12. The method of claim 9, wherein the second die does not overlap the integrated passive device.

13. The method of claim 8 further comprising: prior to removing at least the portion of the substrate, planarizing the molding compound to expose the die stack.

14. The method of claim 13, wherein the molding compound covers top surfaces of the first die after planarizing the molding compound.

15. The method of claim 8, wherein performing the singulation process comprises performing a sawing process on the molding compound, the first redistribution structure, the substrate, and the second redistribution structure.

16. The method of claim 15 further comprising: bonding a third die adjacent to the die stack, the third die being bonded to the top surface of the first redistribution structure using the solderless bonding process, wherein performing the singulation process comprises performing the sawing process between the third die and the die stack.

17. The method of claim 8 further comprising: after the singulation process, bonding the second redistribution structure to a package substrate, wherein the integrated passive device is disposed between the second redistribution structure and the package substrate; and filling an underfill between the second redistribution structure and the package substrate, wherein the underfill is disposed between a lateral surface of the integrated passive device and a solder resist of the package substrate.

18. A method, comprising: forming a first redistribution structure over a substrate, wherein a plurality of through vias extend through the substrate; bonding a first die to a first surface of the first redistribution structure using a solderless bonding process; bonding a second die to the first surface of the first redistribution structure using the solderless bonding process, the second die being adjacent to the first die, wherein the first die and the second die have different heights; bonding a die stack to the first surface of the first redistribution structure using the solderless bonding process, wherein the die stack comprises a plurality of vertically stacked dies, and the die stack is adjacent to the first die and the second die; encapsulating the first die and the second die in a molding compound; and after encapsulating the first die in the molding compound, planarizing the substrate to expose the plurality of through vias; forming a second redistribution structure on a second surface of the substrate, the second surface of the substrate being opposite to the first redistribution structure; and after forming the second redistribution structure, bonding an integrated passive device to a third surface of the second redistribution structure using a solderless bonding process, the third surface of the second redistribution structure being opposite to the substrate, and wherein the first die and the die stack each overlaps the integrated passive device in a cross-sectional view.

19. The method of claim 18, wherein bonding the integrated passive device comprises: directly contacting a second insulating layer of the integrated passive device to a first insulating layer of the second redistribution structure; directly contacting bond pads of the integrated passive device to first metallization patterns, the first metallization patterns being disposed in the first insulating layer; and performing an anneal process to directly bond the second insulating layer to the first insulating layer and to directly bond the bond pads to the first metallization patterns.

20. The method of claim 19, wherein the second die does not overlap the integrated passive device in the cross-sectional view.
